



3DA27

NPN Silicon High Frequency High Power Transistor



Features:

1. Excellent second breakdown capacity. Good characteristic frequency.
2. Amplification factor of small current is great. Good voltage resistance.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for analog computer power output, amplification of high frequency, middle frequency and low frequency, switching circuit.
5. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:

($T_a = 25^\circ\text{C}$)

Parameter name	Symbols	Unit	Specifications	Test Condition
Total Dissipation	P_{tot}	W	50	$T_c: 75^\circ\text{C}$
Max. Collector Current	I_{CM}	A	5	
Junction Temperature	T_{jm}	$^\circ\text{C}$	175	
Storage Temperature	T_{stg}	$^\circ\text{C}$	-55~+175	
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	80~250	$I_c=5\text{mA}$
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	5	$I_E=5\text{mA}$
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	3	$I_c=5\text{A}, I_B=1\text{A}$
Collector-Base Leakage Current	I_{CBO}	mA	0.5	$V_{CB}=20\text{V}$
Collector-Emitter Leakage Current	I_{CEO}	mA	1.0	$V_{CE}=20\text{V}$
Emitter-Base Leakage Current	I_{EBO}	mA	3.0	$V_{EB}=2\text{V}$
DC Current Gain	h_{FE}		10	$V_{CE}=5\text{V}, I_c=1.5\text{A}$
Transition frequency	f_T	MHz	5	$V_{CE}=5\text{V}, I_c=0.5\text{A}$ $f_o=10\text{MHz}$

Outline and Dimensions: